

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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## **JFET Amplifier**

## **P-Channel - Depletion**

### **Features**

• Pb-Free Packages are Available\*

### **MAXIMUM RATINGS**

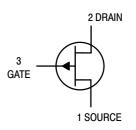
Rating	Symbol	Value	Unit
Drain – Gate Voltage	$V_{DG}$	40	Vdc
Reverse Gate – Source Voltage	$V_{GSR}$	40	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	350 2.8	mW mW/°C
Junction Temperature Range	TJ	-65 to +135	°C
Storage Channel Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



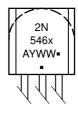
## ON Semiconductor®

### http://onsemi.com





#### **MARKING DIAGRAM**



2N546x = Device Code x = 0, 1, or 2 A = Assembly Location

Y = Year WW = Work Week

■ = Pb–Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•	
Gate – Source Breakdown Voltage $(I_G = 10 \mu Adc, V_{DS} = 0)$	2N5460, 2N5461, 2N5462	V <sub>(BR)GSS</sub>	40	_	_	Vdc
Gate Reverse Current (V <sub>GS</sub> = 20 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = 30 Vdc, V <sub>DS</sub> = 0)	2N5460, 2N5461, 2N5462	I <sub>GSS</sub>	_	-	5.0	nAdc
(V <sub>GS</sub> = 20 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = 20 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C) (V <sub>GS</sub> = 30 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C)	2N5460, 2N5461, 2N5462		_	-	1.0	μAdc
Gate – Source Cutoff Voltage ( $V_{DS}$ = 15 Vdc, $I_D$ = 1.0 $\mu$ Adc)	2N5460 2N5461 2N5462	$V_{GS(off)}$	0.75 1.0 1.8	- - -	6.0 7.5 9.0	Vdc
$\label{eq:Gate-Source Voltage} \begin{split} &(V_{DS} = 15 \text{ Vdc, } I_{D} = 0.1 \text{ mAdc}) \\ &(V_{DS} = 15 \text{ Vdc, } I_{D} = 0.2 \text{ mAdc}) \\ &(V_{DS} = 15 \text{ Vdc, } I_{D} = 0.4 \text{ mAdc}) \end{split}$	2N5460 2N5461 2N5462	$V_{GS}$	0.5 0.8 1.5	- - -	4.0 4.5 6.0	Vdc
ON CHARACTERISTICS						
Zero – Gate – Voltage Drain Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	I <sub>DSS</sub>	-1.0 -2.0 -4.0	- - -	-5.0 -9.0 -16	mAdc
SMALL-SIGNAL CHARACTERISTICS			•	•	•	•
Forward Transfer Admittance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	y <sub>fs</sub>	1000 1500 2000	- - -	4000 5000 6000	μmhos
Output Admittance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f =	1.0 kHz)	y <sub>os</sub>	-	_	75	μmhos
Input Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)		C <sub>iss</sub>	-	5.0	7.0	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)		C <sub>rss</sub>	-	1.0	2.0	pF
FUNCTIONAL CHARACTERISTICS						
Equivalent Short-Circuit Input Noise Voltage (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 100 Hz, BW = 1	l.0 Hz)	e <sub>n</sub>	_	60	115	$nV/\sqrt{Hz}$

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
2N5460	TO-92	1000 Units / Box	
2N5460G	TO-92 (Pb-Free)		
2N5461	TO-92		
2N5461G	TO-92 (Pb-Free)		
2N5461RLRA	TO-92		
2N5461RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
2N5462	TO-92	1000 Units / Box	
2N5462G	TO-92 (Pb-Free)		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# DRAIN CURRENT versus GATE SOURCE VOLTAGE

#### 4.0 $V_{DS} = 15 V$ 3.5 ID, DRAIN CURRENT (mA) 3.0 2.5 $T_A = -55^{\circ}C$ 2.0 25°C 1.5 125°C 1.0 0.5 0 0.2 0.6 8.0 1.0 1.2 1.6 1.8 VGS, GATE-SOURCE VOLTAGE (VOLTS)

Figure 1. V<sub>GS(off)</sub> = 2.0 V

# FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

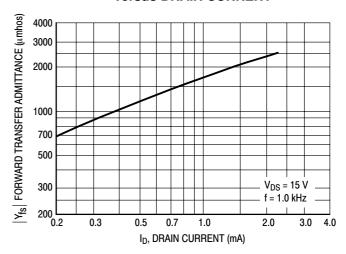


Figure 4. V<sub>GS(off)</sub> = 2.0 V

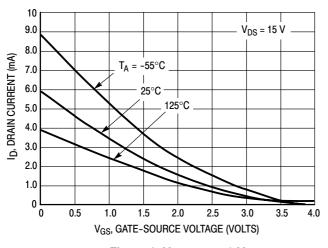


Figure 2. V<sub>GS(off)</sub> = 4.0 V

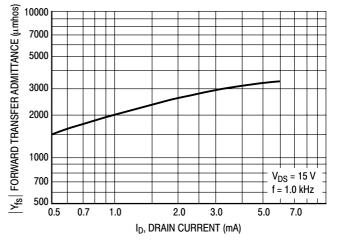


Figure 5. V<sub>GS(off)</sub> = 4.0 V

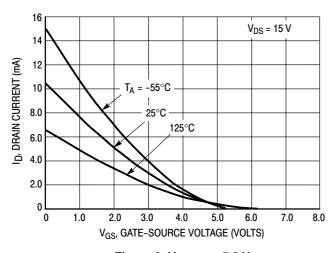


Figure 3.  $V_{GS(off)} = 5.0 \text{ V}$ 

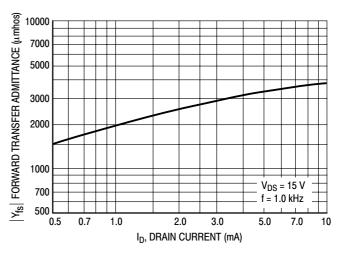


Figure 6.  $V_{GS(off)} = 5.0 \text{ V}$ 

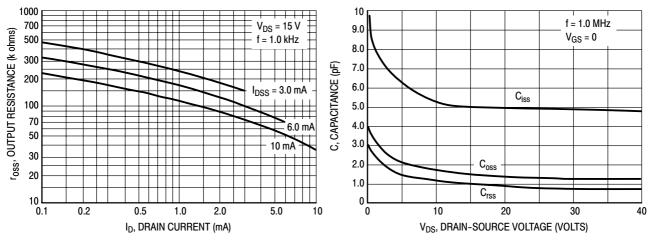


Figure 7. Output Resistance versus Drain Current

Figure 8. Capacitance versus Drain-Source Voltage

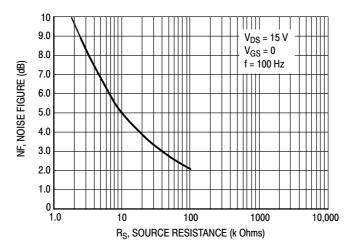
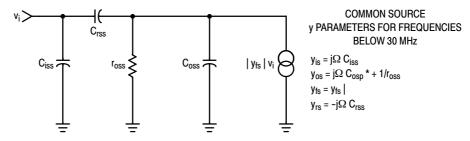


Figure 9. Noise Figure versus Source Resistance



 $^{\star}C_{osp}$  is  $C_{oss}$  in parallel with Series Combination of  $C_{iss}$  and  $C_{rss}$ .

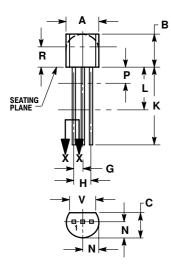
#### NOTE:

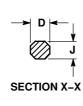
 Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 10. Equivalent Low Frequency Circuit

#### PACKAGE DIMENSIONS

TO-92 CASE 29-11 ISSUE AL





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  VIA EM 1092
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
v	0 135		3 43		

STYLE 7:

PIN 1. SOURCE

- 2. DRAIN
- 3. GATE

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